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NTLJS4159N

Power MOSFET

30 V, 7.8 A, Single N-Channel, 2x2 mm
WDFN Package

Features

- WDFN Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- 2x2 mm Footprint Same as SC-88
- Lowest $R_{DS(on)}$ in 2x2 mm Package
- 1.8 V $R_{DS(on)}$ Rating for Operation at Low Voltage Logic Level Gate Drive
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments
- This is a Pb-Free Device

Applications

- DC-DC Conversion
- Boost Circuits for LED Backlights
- Optimized for Battery and Load Management Applications in Portable Equipment such as, Cell Phones, PDA's, Media Players, etc.
- Low Side Load Switch

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | | | Symbol | Value | Unit |
|---|------------------------|----------------------------|----------------------------|------------|--------------------|
| Drain-to-Source Voltage | | | V_{DSS} | 30 | V |
| Gate-to-Source Voltage | | | V_{GS} | ± 8.0 | V |
| Continuous Drain Current (Note 1) | Steady State | $T_A = 25^{\circ}\text{C}$ | I_D | 6.0 | A |
| | | $T_A = 85^{\circ}\text{C}$ | | 4.4 | |
| | $t \leq 5 \text{ s}$ | $T_A = 25^{\circ}\text{C}$ | | 7.8 | |
| Power Dissipation (Note 1) | Steady State | $T_A = 25^{\circ}\text{C}$ | P_D | 1.92 | W |
| | $t \leq 5 \text{ s}$ | | | 3.3 | |
| Continuous Drain Current (Note 2) | Steady State | $T_A = 25^{\circ}\text{C}$ | I_D | 3.6 | A |
| | | $T_A = 85^{\circ}\text{C}$ | | 2.6 | |
| Power Dissipation (Note 2) | | | $T_A = 25^{\circ}\text{C}$ | P_D | 0.70 |
| Pulsed Drain Current | $t_p = 10 \mu\text{s}$ | | I_{DM} | 28 | A |
| Operating Junction and Storage Temperature | | | T_J, T_{STG} | -55 to 150 | $^{\circ}\text{C}$ |
| Source Current (Body Diode) (Note 2) | | | I_S | 3.0 | A |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | | | T_L | 260 | $^{\circ}\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

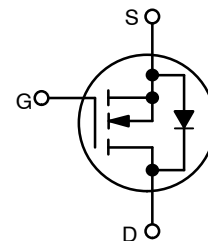
1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size of 30 mm², 2 oz Cu.



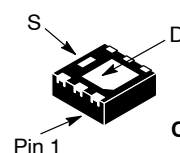
ON Semiconductor®

www.onsemi.com

| $V_{(BR)DS}$ | $R_{DS(on)}$ MAX | I_D MAX (Note 1) |
|--------------|-----------------------|--------------------|
| 30 V | 35 m Ω @ 4.5 V | 7.8 A |
| | 45 m Ω @ 2.5 V | |
| | 55 m Ω @ 1.8 V | |



N-CHANNEL MOSFET



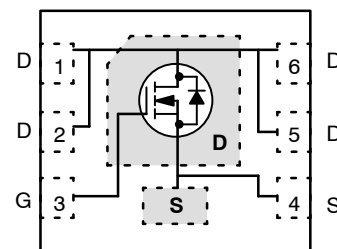
WDFN6
CASE 506AP

MARKING DIAGRAM



JB = Specific Device Code
M = Date Code
■ = Pb-Free Package
(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

| Device | Package | Shipping† |
|---------------|-----------------|------------------|
| NTLJS4159NT1G | WDFN6 (Pb-Free) | 3000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Max | Unit |
|---|-----------------|-----|------|
| Junction-to-Ambient – Steady State (Note 3) | $R_{\theta JA}$ | 65 | °C/W |
| Junction-to-Ambient – $t \leq 5$ s (Note 3) | $R_{\theta JA}$ | 38 | |
| Junction-to-Ambient – Steady State Min Pad (Note 4) | $R_{\theta JA}$ | 180 | |

3. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
4. Surface Mounted on FR4 Board using the minimum recommended pad size (30 mm², 2 oz Cu).

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|-------------------|--|--------------------------|-----|-----------|---------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 30 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$, Ref to 25°C | | 20 | | mV/°C |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$ | $T_J = 25^\circ\text{C}$ | | 1.0 | μA |
| | | | $T_J = 65^\circ\text{C}$ | | 1.0 | |
| | | | $T_J = 85^\circ\text{C}$ | | 5.0 | |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 8.0\text{ V}$ | | | ± 100 | nA |

ON CHARACTERISTICS (Note 5)

| | | | | | | |
|---|------------------|---|-----|------|-----|------------|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ | 0.4 | 0.7 | 1.0 | V |
| Negative Gate Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | 3.18 | | mV/°C |
| Drain-to-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = 4.5\text{ V}, I_D = 2.0\text{ A}$ | | 20.3 | 35 | m Ω |
| | | $V_{GS} = 2.5\text{ V}, I_D = 2.0\text{ A}$ | | 25.8 | 45 | |
| | | $V_{GS} = 1.8\text{ V}, I_D = 1.8\text{ A}$ | | 35.2 | 55 | |
| Forward Transconductance | g_{FS} | $V_{DS} = 16\text{ V}, I_D = 2.0\text{ A}$ | | 5.3 | | S |

CHARGES, CAPACITANCES AND GATE RESISTANCE

| | | | | | | |
|------------------------------|--------------|---|--|-------|----|----------|
| Input Capacitance | C_{ISS} | $V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 15\text{ V}$ | | 1045 | | pF |
| Output Capacitance | C_{OSS} | | | 115.5 | | |
| Reverse Transfer Capacitance | C_{RSS} | | | 45.3 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 2.0\text{ A}$ | | 12.1 | 13 | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | 1.2 | | |
| Gate-to-Source Charge | Q_{GS} | | | 1.9 | | |
| Gate-to-Drain Charge | Q_{GD} | | | 2.7 | | |
| Gate Resistance | R_G | | | 3.65 | | Ω |

SWITCHING CHARACTERISTICS (Note 6)

| | | | | | | |
|---------------------|--------------|--|--|------|--|----|
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS} = 4.5\text{ V}, V_{DD} = 15\text{ V}, I_D = 2.0\text{ A}, R_G = 3.0\text{ }\Omega$ | | 6.8 | | ns |
| Rise Time | t_r | | | 12.4 | | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | 26 | | |
| Fall Time | t_f | | | 5.1 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|--------------------------|----------|--|---------------------------|--|------|-----|----|
| Forward Recovery Voltage | V_{SD} | $V_{GS} = 0\text{ V}, I_S = 2.0\text{ A}$ | $T_J = 25^\circ\text{C}$ | | 0.71 | 1.2 | V |
| | | | $T_J = 125^\circ\text{C}$ | | 0.58 | | |
| Reverse Recovery Time | t_{RR} | $V_{GS} = 0\text{ V}, dI_{SD}/dt_i = 100\text{ A}/\mu\text{s}, I_S = 1.0\text{ A}$ | | | 15 | 35 | ns |
| Charge Time | t_a | | | | 9.0 | | |
| Discharge Time | t_b | | | | 6.0 | | |
| Reverse Recovery Time | Q_{RR} | | | | 7.0 | | nC |

5. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

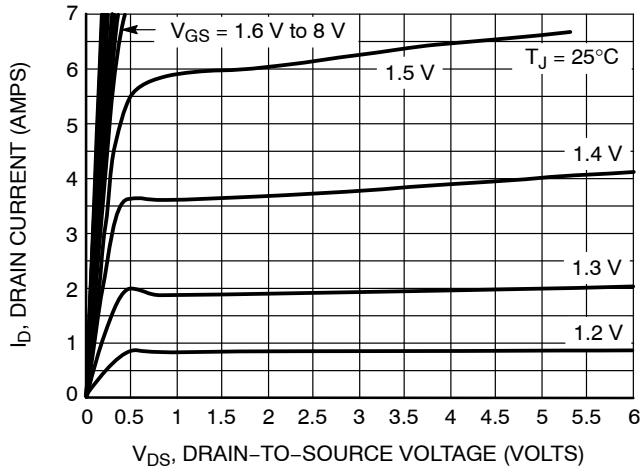


Figure 1. On-Region Characteristics

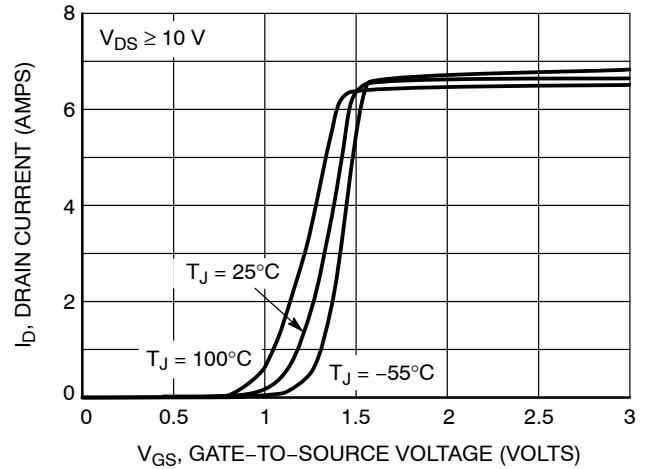


Figure 2. Transfer Characteristics

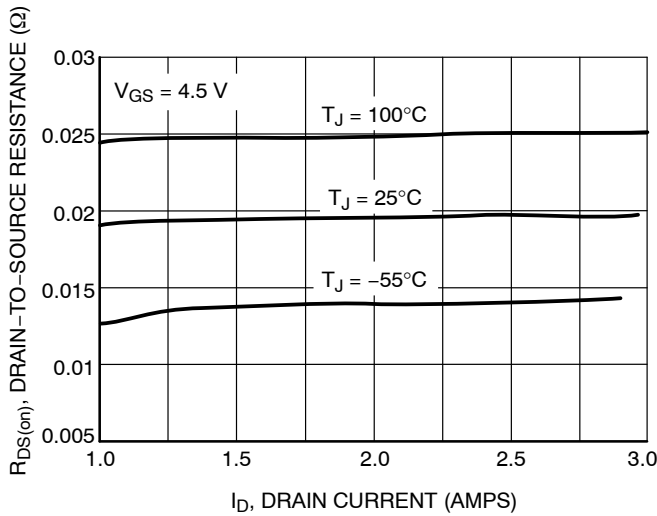


Figure 3. On-Resistance versus Drain Current

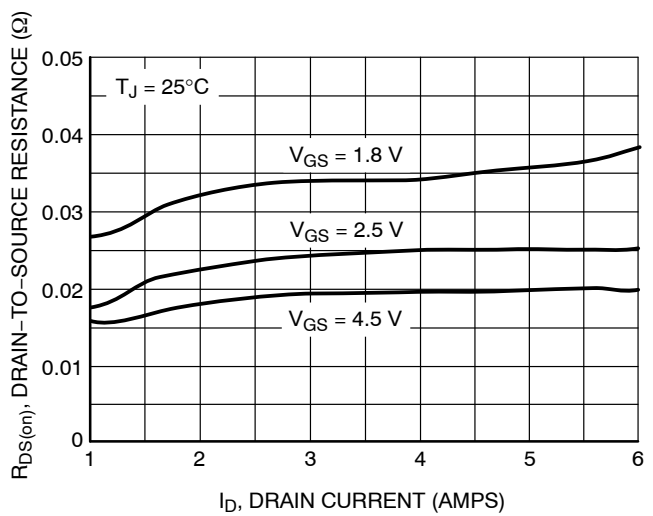


Figure 4. On-Resistance versus Drain Current and Gate Voltage

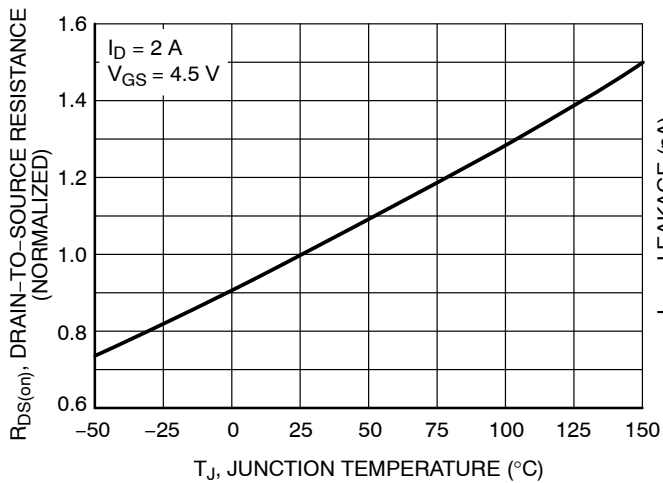


Figure 5. On-Resistance Variation with Temperature

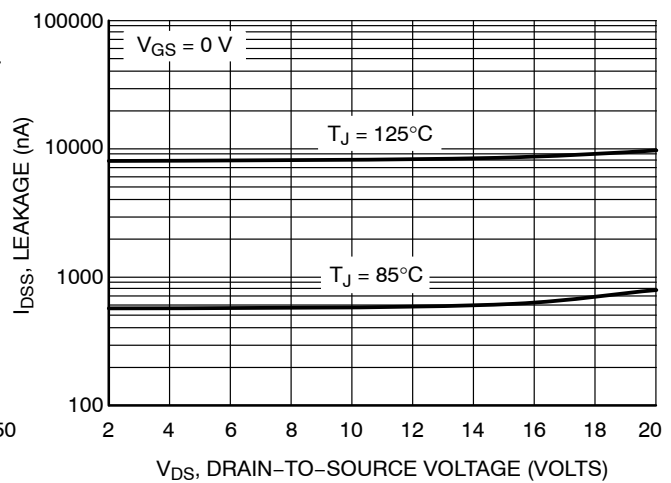


Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

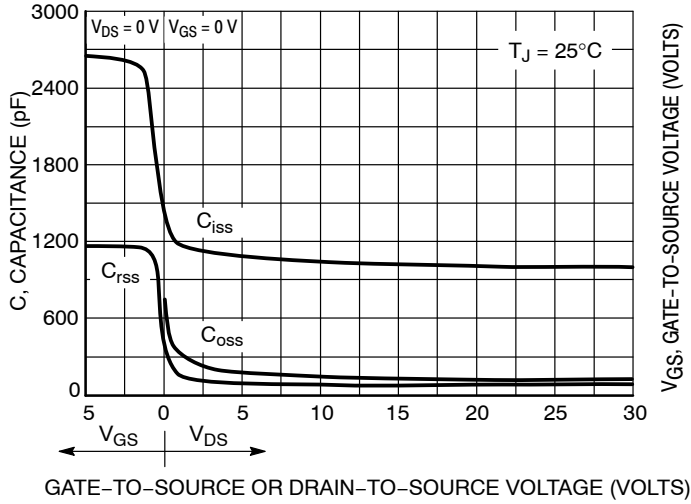


Figure 7. Capacitance Variation

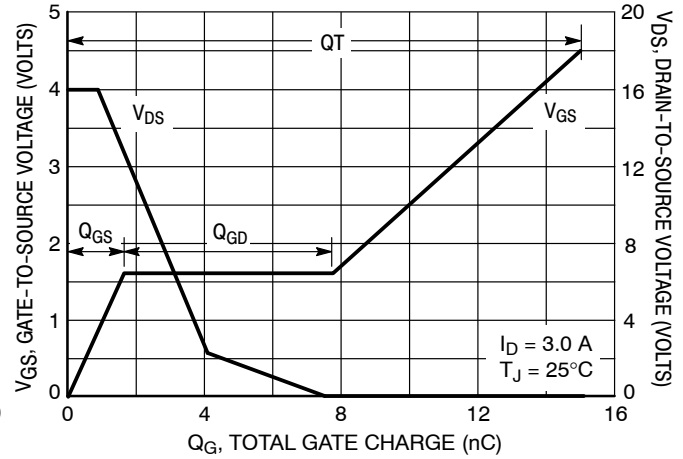


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

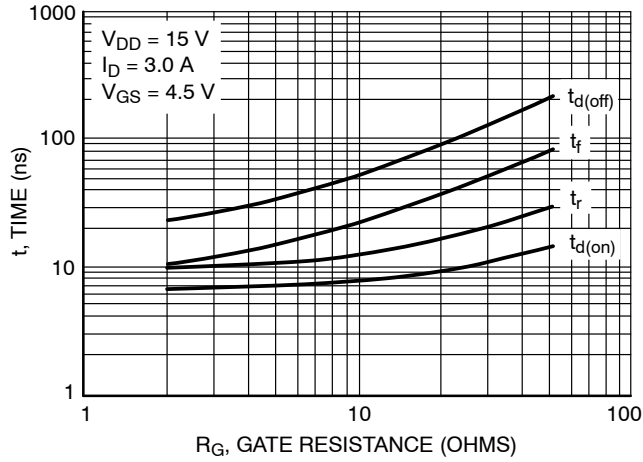


Figure 9. Resistive Switching Time Variation versus Gate Resistance

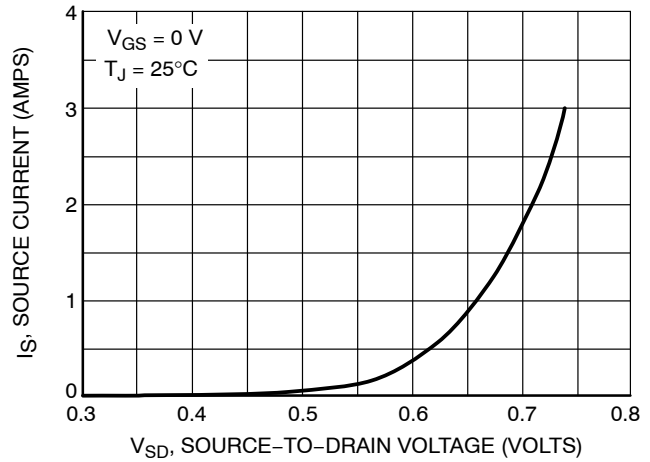


Figure 10. Diode Forward Voltage versus Current

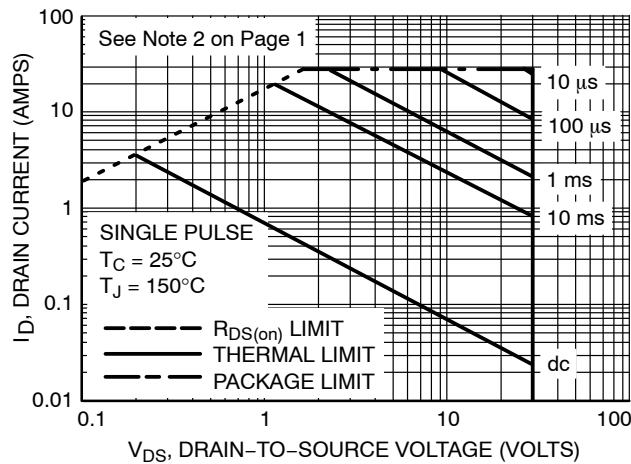


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

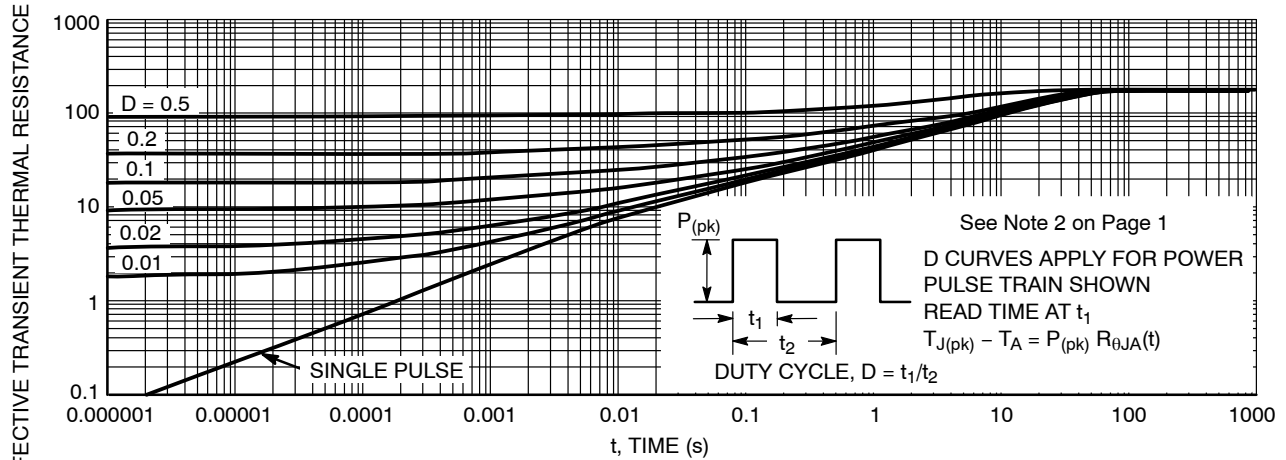
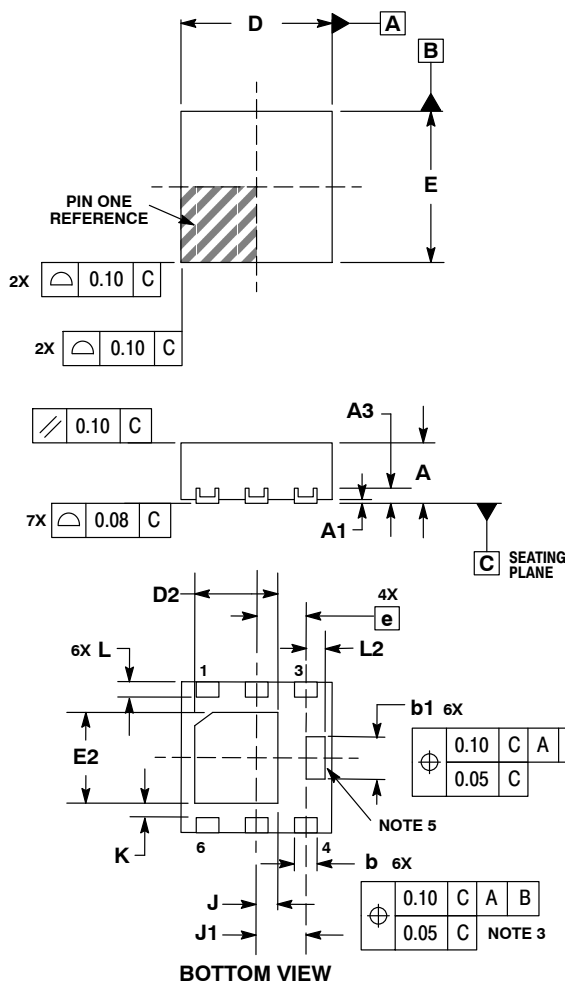


Figure 12. Thermal Response

NTLJS4159N

PACKAGE DIMENSIONS

WDFN6 2x2 CASE 506AP ISSUE B

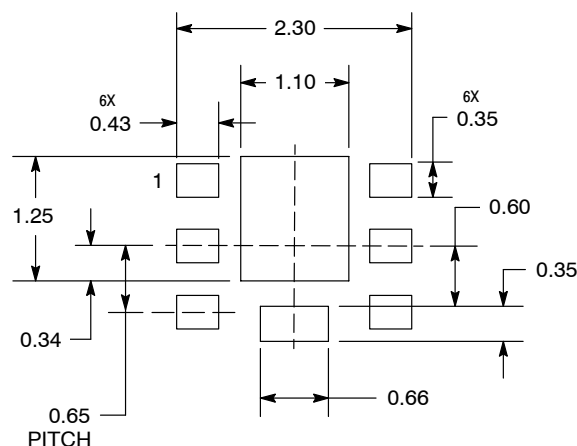


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. CENTER TERMINAL LEAD IS OPTIONAL. TERMINAL LEAD IS CONNECTED TO TERMINAL LEAD # 4.
6. PINS 1, 2, 5 AND 6 ARE TIED TO THE FLAG.

| DIM | MILLIMETERS | |
|-----|-------------|------|
| | MIN | MAX |
| A | 0.70 | 0.80 |
| A1 | 0.00 | 0.05 |
| A3 | 0.20 REF | |
| b | 0.25 | 0.35 |
| b1 | 0.51 | 0.61 |
| D | 2.00 BSC | |
| D2 | 1.00 | 1.20 |
| E | 2.00 BSC | |
| E2 | 1.10 | 1.30 |
| e | 0.65 BSC | |
| K | 0.15 REF | |
| L | 0.20 | 0.30 |
| L2 | 0.20 | 0.30 |
| J | 0.27 REF | |
| J1 | 0.65 REF | |

SOLDERMASK DEFINED MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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